

#### 40V 175°C DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

BVDSS	Rds(ON) Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C		
40V	$12.3 \text{m}\Omega$ @ $V_{GS} = 10V$	46.2A		
40 V	$17.5 \text{m}\Omega$ @ V <sub>GS</sub> = $4.5 \text{V}$	38.7A		

## **Description and Applications**

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Motor Control
- Power Management Functions
- DC-DC Converters

## **Features and Benefits**

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching, Test in Production

  Ensures
  More Reliable and Robust End Application
- High Conversion Efficiency
- Low Rds(ON) Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- Wettable Flank for Improved Optical Inspection
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMTH4008LPDWQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

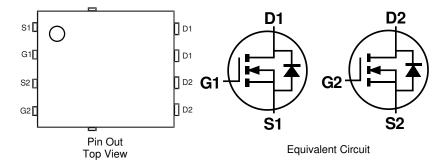
#### **Mechanical Data**

- Case: PowerDI<sup>®</sup>5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 🚱
- Weight: 0.097 grams (Approximate)

### PowerDI5060-8/SWP (Type UXD)



Top View Bottom View



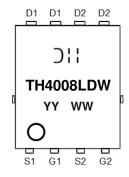
## **Ordering Information** (Note 4)

Part Number	Case	Packaging
DMTH4008LPDWQ-13	PowerDI5060-8/SWP (Type UXD)	2,500/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See http://www.diodes.com/quality/lead\_free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**



);; = Manufacturer's Marking
TH4008LDW = Product Type Marking Code
YYWW or \(\forall Y\) WW = Date Code Marking
YY or \(\forall Y\) = Year (ex: 20 = 2020)
WW = Week (01 to 53)



# **Maximum Ratings** (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V <sub>DSS</sub>	40	V	
Gate-Source Voltage	V <sub>GSS</sub>	±20	V	
Continuous Drain Current (Note 5)	T <sub>A</sub> = +25°C T <sub>A</sub> = +100°C	lo	10.0 7.1	А
Continuous Drain Current (Note 6) $ T_{C} = +25^{\circ}C $ $ T_{C} = +100^{\circ}C $		I <sub>D</sub>	46.2 32.7	А
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	184	Α	
Maximum Continuous Body Diode Forward Current (Note 6)	Is	43.7	Α	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 19	I <sub>SM</sub>	184	Α	
Avalanche Current, L = 0.1mH		las	23.1	Α
Avalanche Energy, L = 0.1mH		Eas	26.6	mJ

## **Thermal Characteristics**

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5) $T_A = +25^{\circ}C$		PD	2.67	W
Thermal Resistance, Junction to Ambient (Note 5)	Reja	56.6	°C/W	
Total Power Dissipation (Note 6) $T_C = +25^{\circ}C$		PD	39.4	W
Thermal Resistance, Junction to Case (Note 6)		Rejc	3.8	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +175	°C

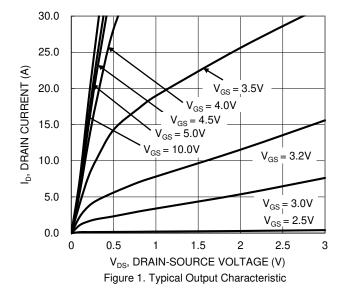
## **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

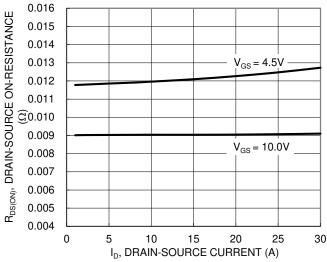
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage		40	_	_	V	$V_{GS} = 0V, I_{D} = 250\mu A$	
Zero Gate Voltage Drain Current	IDSS	_	_	1	μΑ	V <sub>DS</sub> = 32V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1.2	1.88	2.3	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
Static Drain-Source On-Resistance	Б	_	9.5	12.3	mΩ	VGS = 10V, ID = 20A	
Static Diam-Source On-nesistance	RDS(ON)	_	11.9	17.5	mΩ	$V_{GS} = 4.5V, I_{D} = 10A$	
Diode Forward Voltage	$V_{SD}$	_	0.9	1.2	V	$V_{GS} = 0V, I_S = 20A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	_	881	_	pF	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V, f = 1MHz	
Output Capacitance	Coss	_	496	_	pF		
Reverse Transfer Capacitance	Crss	_	19.5	_	pF		
Gate Resistance	Rg	_	2.06	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (VGS = 10V)	Qg	_	12.3	_	nC		
Total Gate Charge (VGS = 4.5V)	Qg	_	5.8	_	nC	\/ 00\/ I- 00A	
Gate-Source Charge	Qgs	_	2.6	_	nC	$V_{DS} = 20V, I_{D} = 20A$	
Gate-Drain Charge	Qgd	_	1.6	_	nC	1	
Turn-On Delay Time	t <sub>D(ON)</sub>	_	3.82	_	ns		
Turn-On Rise Time	tr	_	4.76	_	ns	$\begin{aligned} V_{DD} &= 20 V, \ V_{GS} = 10 V, \\ R_g &= 3 \Omega, \ I_D = 20 A \end{aligned}$	
Turn-Off Delay Time	tD(OFF)	_	12.6	_	ns		
Turn-Off Fall Time	tF	_	4.83	_	ns		
Body Diode Reverse Recovery Time	trr	_	31.9	_	ns		
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	_	25.0	_	nC		

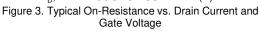
5. Device mounted on FR-4 substrate PC board, 2oz. copper, with thermal bias to bottom layer 1inch square copper plate.

<sup>5.</sup> Device involved on the substance of board, 202. copper, with thermal blas to
6. Thermal resistance from junction to soldering point (on the exposed drain pad).
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.









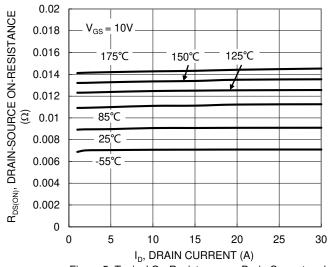
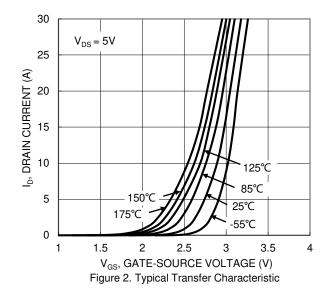
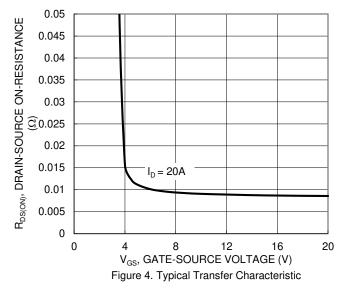


Figure 5. Typical On-Resistance vs. Drain Current and Temperature





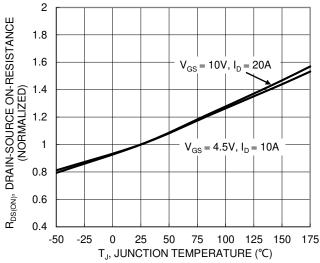


Figure 6. On-Resistance Variation with Temperature





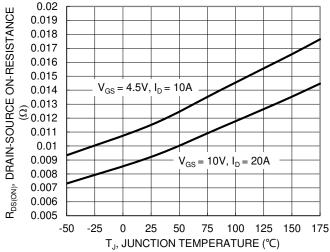
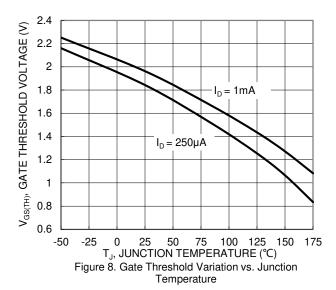
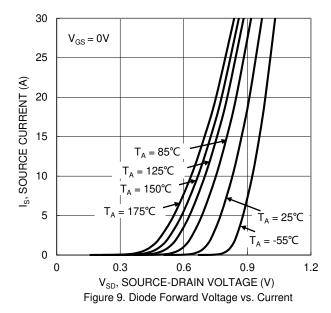


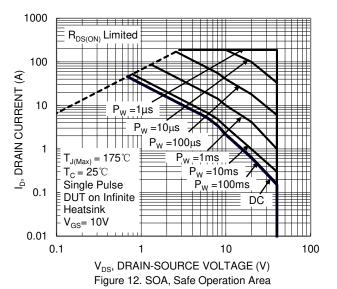
Figure 7. On-Resistance Variation with Temperature





10
8 6  $\searrow$  9 4  $V_{DS} = 20V, I_{D} = 20A$  Qg (nC)Figure 11. Gate Charge

10000 f=1MHz C<sub>T</sub>, JUNCTION CAPACITANCE (pF)  $C_{iss}$ 1000  $\mathsf{C}_{\mathsf{oss}}$ 100 10 0 10 15 20 25 30 35 40  $V_{DS}$ , DRAIN-SOURCE VOLTAGE (V) Figure 10. Typical Junction Capacitance





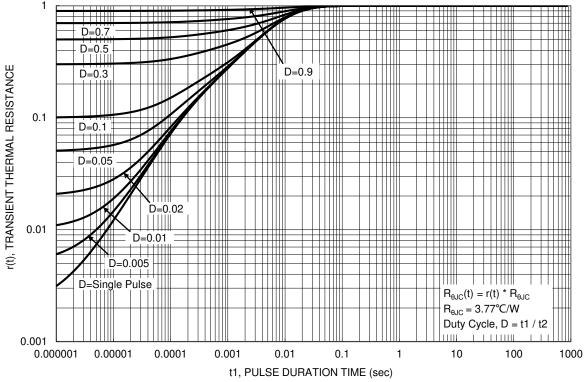


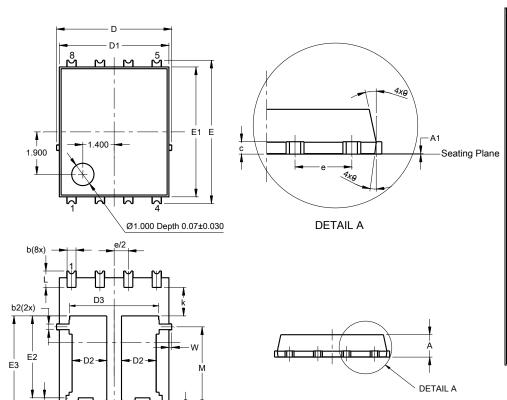
Figure 13. Transient Thermal Resistance



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### PowerDI5060-8/SWP (Type UXD)

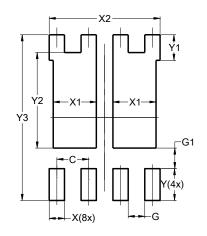


PowerDI5060-8/SWP					
(Type UXD)					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
<b>A</b> 1	0.00	0.05			
b	0.30	0.50	0.41		
b2	0.20	0.35	0.25		
b4		).25REF			
С	0.230	0.330	0.277		
D		.15 BS0	5		
D1	4.70	5.10	4.90		
D2	1.46	1.66	1.55		
D3	3.78	4.18	3.98		
E	6	.40 BS0	3		
E1	5.60	6.00	5.80		
E2	3.46	3.86	3.66		
E2a	4.195	4.595	4.395		
е	1	.27BSC	)		
k	1.05				
L	0.635	0.835	0.735		
La	0.635	0.835	0.735		
L1	0.200	0.400	0.300		
M	3.205	4.005	3.605		
W	0.025	0.225	0.125		
θ	10°	12°	11°		
θ1	6°	8°	7°		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### PowerDI5060-8/SWP (Type UXD)



Dimensions	Value (in mm)		
С	1.270		
G	0.660		
G1	0.820		
X	0.610 1.720 4.420		
X1			
X2			
Υ	1.270		
Y1	1.020		
Y2	3.810		
Y3	6.610		



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